PATENT COOPERATION TREATY

PCT

INTERNATIONAL PRELIMINARY REPORT ON PATENTABILITY

(Chapter II of the Patent Cooperation Treaty)
(PCT Article 36 and Rule 70)

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Applicant's or agent's file reference	FOR FURTHER ACTION		See Form PCT/IPEA/416	
CF017975WO				
International application No.	International filing date (day/mor	nth/year)	Priority date (day/month/year	03
PCT/JP2004/004072	24.03.20	04	26.03.20	03
International Patent Classification (IPC) of Int.Cl. 7 HO1L 31/06	r national classification and IF	PC .		
Applicant CANON KABUSHIKI KA	ISHA			·
and/or sheets c Administrative sheets which s beyond the dis Supplemental b. a total of (indicate type	of4 sheets, included to the approximation of4 sheets, included a sheets, as follows: escription, claims and/or draw ontaining rectifications authority instructions). upersede earlier sheets, but we inclosure in the international approximation of electronic care.	ings which have rized by this Authorication as filed	been amended and are the bas nority (see Rule 70.16 and Sec ty considers contain an amend I, as indicated in item 4 of Bo	is of this report ction 607 of the diment that goes in No. I and the diment that goes indicated in the
containing a sequence listing and/or tables related thereto, in computer relations for the computer relations for the sequence Listing (see Section 802 of the Administrative Instructions). 4. This report contains indications relating to the following items:				
1	the report			
Box No. II Priority				nlicability
Box No. III Non-esta	ablishment of opinion with reg	ard to novelty, inventive step and industrial applicability with regard to novelty, inventive step or industrial applicability;		
₩ Box No. IV Lack of	unity of invention			
citations	and explanations supporting	 with regard to r such statement 	novelty, inventive step of indus	ula appadomy,
	documents cited			
Box No VII Certain defects in the international application				
Box No. VIII Certain	observations on the internation	n'al application		
			ion of this report	
Date of submission of the demand 19.10.20	004	. Date of combier	16.08.2005	
Name and mailing address of the IPE	A/IP	Authorized offi	cer	2K 9207
Japan Patent O	ffice Tokyo 100-8915, Japan	Telephone No.	+81-3-3581-1101 Ext.	3255

INTERNATIONAL PRELIMINARY REPORT ON PATENTABILITY

International application No.

PCT/JP2004/004072

k No. I	Basis of the report	·
With	regard to the language, this report is based of	on the international application in the language in which it was filed, unless
	· · · · · · · · · · · · · · · · · · ·	l l
	This report is based on translations from the	original language into the following language,
•	which is the language of a translation furn international search (under Rules 12.3 a	and 23.1(b))
	publication of the international applicat	tion (under Rule 12.4)
	international preliminary examination ((under Rules 55.2 and/or 55.3)
With	regard to the elements of the international	application, this report is based on (replacement sheets which have been invitation under Article 14 are referred to in this report as "originally filed"
furni	ished to the receiving Office in response to ar	invitation under Afficie 14 die 1961 122 1
and	are not annexed to this report):	
Γ	the international application as originally	filed/furnished -
V	the description:	as originally filed/furnished
	pages 1-48	
	pages*	received by this Authority on received by this Authority on
	pages*	received by this Authority on
V	the claims:	as originally filed/furnished
	pages 2-4	
	pages*	received by this Authority on 19.10.2004
	pages* 1	received by this Authority on
	pages*	received by this Authority on
₩.	the drawings:	as originally filed/furnished
	pages 1-6	
	pages*	received by this Authority on
	pages*	received by this Authority on
Γ	a sequence listing and/or any related tab	ele(s) - see Supplemental Box Relating to Sequence Listing.
3. [The amendments have resulted in the car	ncellation of:
	the description, pages	
	the claims, Nos.	
	the drawings sheets/figs	· · · · · · · · · · · · · · · · · · ·
	the sequence listing (specify):	
		isting (specify):
4.	made, since they have been considered (Rule 70.2(c)).	some of) the amendments annexed to this report and listed below had not been done to go beyond the disclosure as filed, as indicated in the Supplemental Bo
	the description, pages	
	the claims, Nos.	· · · · · · · · · · · · · · · · · · ·
•	the drawings, sheets/figs	
	the sequence listing (specify):	
	any table(s) related to sequence	
	item 4 applies, some or all of those sheets ma	·

INTERNATIONAL PRELIMINARY REPORT ON PATENTABILITY

International application No.

PCT/JP2004/004072

Box 1	No. IV	Lack of unity of invention		
1.	In rest	conse to the invitation to restrict or pay additional fees the applicant has:		
restricted the claims.				
		paid additional fees.		
		paid additional fees under protest.		
		neither restricted nor paid additional fees.		
2.		This Authority found that the requirement of unity of invention is not complied with and chose, according to Rule 68.1, not to invite the applicant to restrict or pay additional fees.		
3.	This	Authority considers that the requirement of unity of invention in accordance with Rule 13.1, 13.2 and 13.3 is:		
1		complied with.		
	V	not complied with for the following reasons:		
Common technical features between two independent claims 1 and 4 in this application reside only in a polycrystalline silicon material (layer/substrate), and a layer having an amorphous silicon phase and microcrystalline silicon phase on the polycrystalline silicon material. The remaining features of claims 1 and 4 are not considered to silicon phase on the polycrystalline silicon material. The remaining features of claims 1 and 4 are not considered to involve the same technical meaning. Furthermore, D1 (JP 2001-217442 A) discloses a solar cell having an n-type polycrystalline silicon layer (2) on a SUS substrate (1) (e.g. Fig 1), where the n-type polycrystalline silicon layer (2) could be replaced with a microcrystalline layer ([0010]), and a metal grade silicon substrate could be used in place of the SUS substrate (1) ([0014]), which substantially correspond to the common technical features above. Therefore, claims 1-3 and 4 do not involve same or corresponding special technical features within the meaning of				
P	CT Ru	de 13.2.		
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	4. C	Consequently, this report has been established in respect of the following parts of the international application:		
		all parts.	1	
		the parts relating to claims Nos.	1	
- 1				

INTERNATIONAL PRELIMINARY REPORT ON PATENTABILITY

International application No.
PCT/JP2004/004072

Box No. V	Reasoned statement under Article 35(2) with regard to novelty, inventive step or industrial applicability; citations and explanations supporting such statement				
1. Statement	t elty (N)	Claims Claims	1-4	YES NO	
Inve	entive step (IS)	Claims Claims	1-4	YES NO	
Indu	ustrial applicability (IA)	Claims Claims	1-4	YES NO	
			<u> </u>		

Citations and explanations(Rule 70.7)

D1: JP 2001-217442 A (Hitachi Cable) 2001.08.10

- (1) D1 discloses a solar cell having an n-type polycrystalline silicon layer (2) on a SUS substrate (1) (e.g. Fig.1), where the n-type polycrystalline silicon layer (2) could be replaced with a microcrystalline layer ([0010]), and a metal grade silicon substrate could be used in place of the SUS substrate (1) ([0014]).
- (2) Regarding claims 1-3, although a polycrystalline silicon layer (2) in D1 is not a non-doped layer as claim 1, it is not clear from the description or other evidence what a technical meaning this difference of doping has. Each limitation by claims 2-3 is also considered to be merely a matter of design. Therefore, claims 1-3 are considered to be lack of inventive step over D1.
- (3) Regarding <u>claim 4</u>, the term "grown with the microcrystalline silicon phase as a seed" in this claim does not limit this product claim. Therefore, claim 4 is also not considered to involve inventive step, since no clearly distinguishable technical features from D1 could be found.

CLAIMS

(Amended) A solar cell comprising:

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a silicon substrate for a solar cell, the substrate comprising a base composed of a polycrystalline metal-grade silicon solidified in one direction and a high-purity polycrystalline silicon layer stacked on a surface of the base; and

a non-doped layer stacked on the silicon substrate, the non-doped layer having an amorphous silicon phase and a microcrystalline silicon phase mixed together.

- 2. (Unchanged) A solar cell according to claim

 1, wherein a thickness of the layer having the nondoped amorphous silicon phase and the
- 15 microcrystalline silicon phase mixed together ranges from 1 nm to 15 nm.
 - 3. (Unchanged) A solar cell according to claim 1 or 2, wherein a ratio of the amorphous silicon phase and the microcrystalline silicon phase in the layer having the non-doped amorphous silicon phase and the microcrystalline silicon phase mixed together ranges from 1:1 to 10:1.
- 4. (Unchanged) A solar cell comprising a crystalline silicon substrate or a crystalline silicon layer, a layer having an amorphous silicon phase and a microcrystalline silicon phase mixed together, and a polycrystalline silicon layer grown with the microcrystalline silicon phase as a seed, which are stacked in mentioned order.